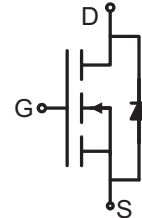
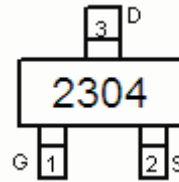


N-Channel Enhancement Mode Power MOSFET
Description

The RM3A6N30S2 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications.


Schematic diagram

Marking and pin assignment

SOT-23 top view
General Features

- $V_{DS} = 30V, I_D = 3.6A$
- $R_{DS(ON)} < 73m\Omega @ V_{GS}=4.5V$
- $R_{DS(ON)} < 58m\Omega @ V_{GS}=10V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- Battery protection
- Load switch
- Power management

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2304	RM3A6N30S2	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	3.6	A
Drain Current-Pulsed (Note 1)	I_{DM}	15	A
Maximum Power Dissipation	P_D	1.7	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	73.5	$^\circ C/W$
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Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA

Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.5	2.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=3.1A$	-	58	73	m Ω
		$V_{GS}=10V, I_D=3.6A$	-	40	58	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=3.6A$	-	11	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{ISS}	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0MHz$	-	230	-	PF
Output Capacitance	C_{OSS}		-	40	-	PF
Reverse Transfer Capacitance	C_{RSS}		-	17	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=3.6A$ $V_{GS}=4.5V, R_{GEN}=6\Omega$	-	10	-	nS
Turn-on Rise Time	t_r		-	50	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	10	-	nS
Turn-Off Fall Time	t_f		-	20	-	nS
Total Gate Charge	Q_g	$V_{DS}=15V, I_D=3.6A,$ $V_{GS}=10V$	-	4.0	-	nC
Gate-Source Charge	Q_{gs}		-	0.75	-	nC
Gate-Drain Charge	Q_{gd}		-	0.65	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=2.7A$	-	0.8	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	1.6	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

RATING AND CHARACTERISTICS CURVES (RM3A6N30S2)

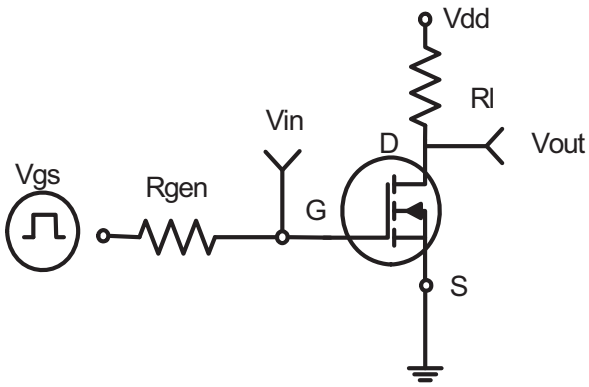


Figure 1: Switching Test Circuit

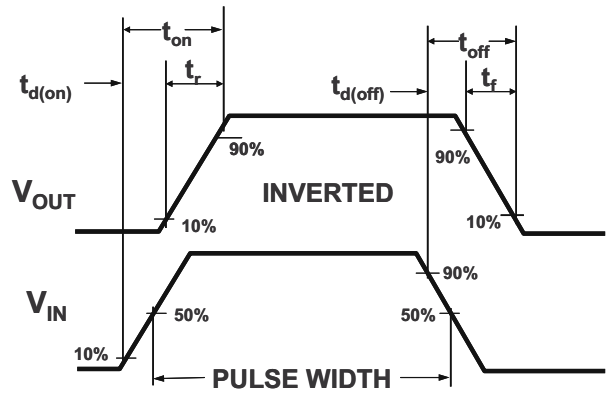
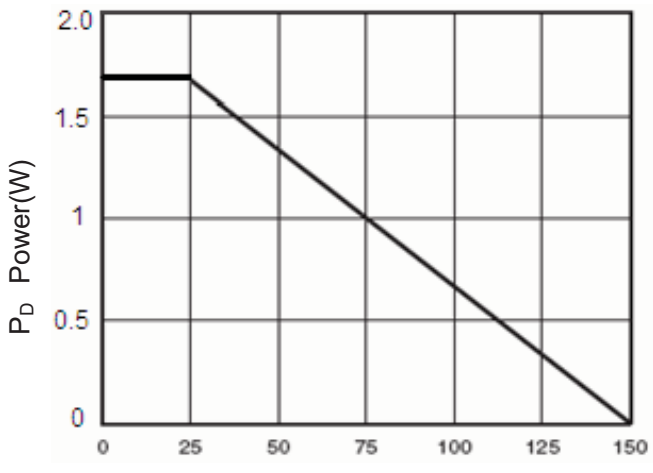
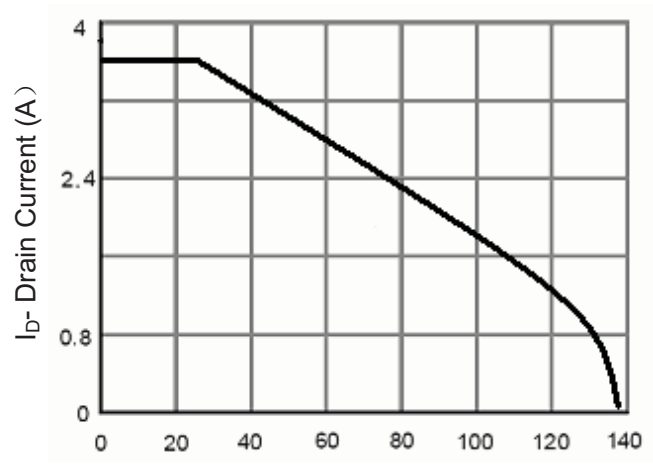


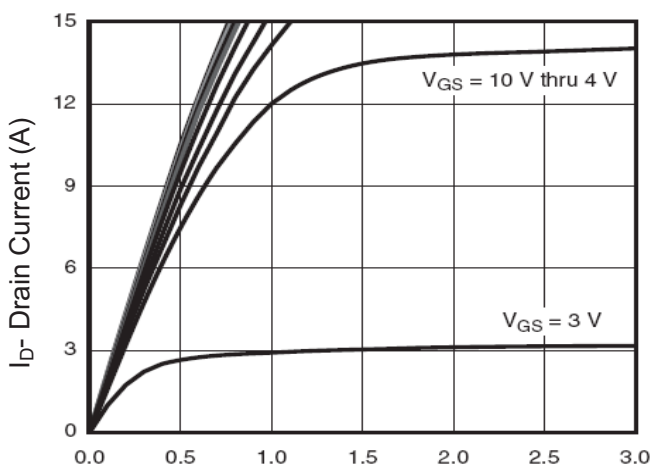
Figure 2: Switching Waveforms



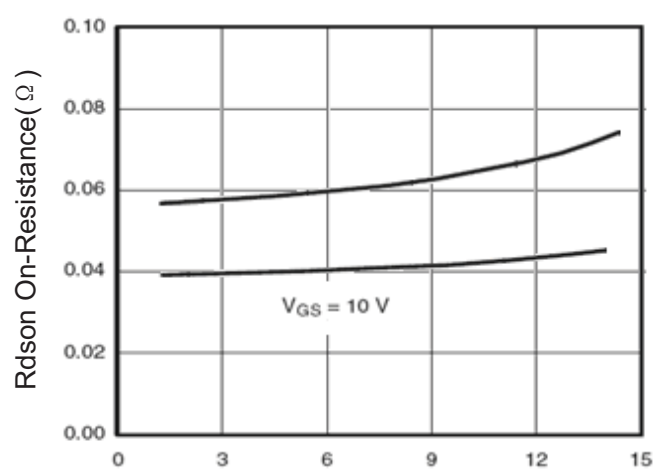
T_J-Junction Temperature(°C)
Figure 3 Power Dissipation



T_J-Junction Temperature(°C)
Figure 4 Drain Current

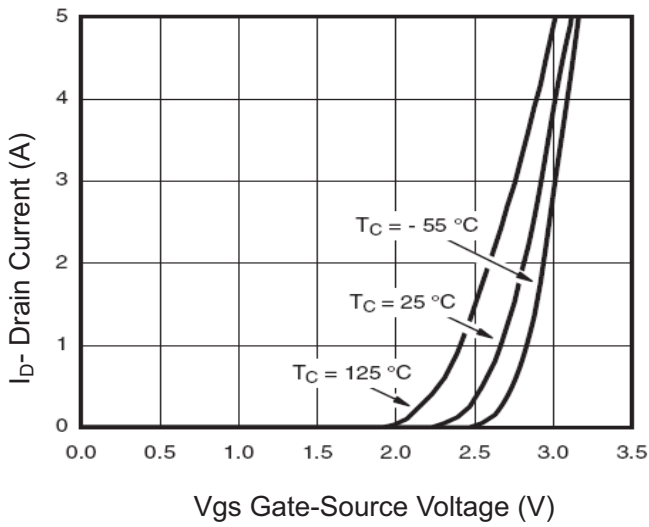


V_{ds} Drain-Source Voltage (V)
Figure 5 Output Characteristics

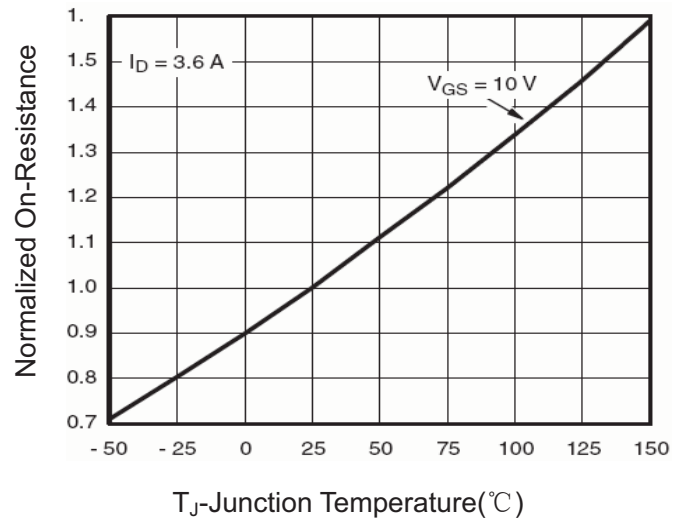


I_D Drain Current (A)
Figure 6 Drain-Source On-Resistance

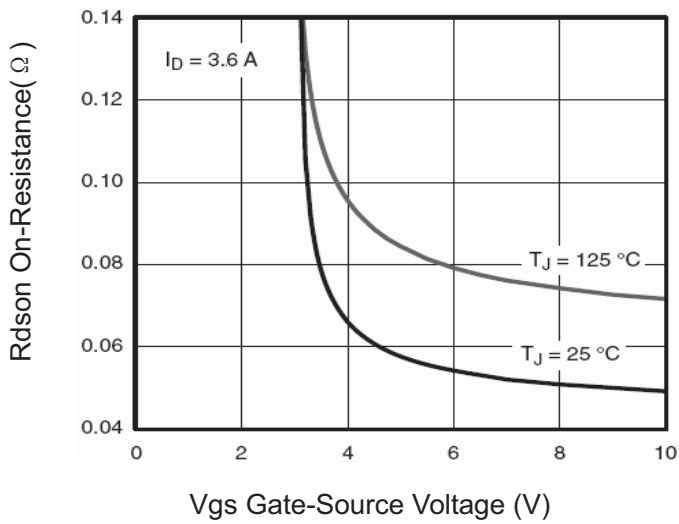
RATING AND CHARACTERISTICS CURVES (RM3A6N30S2)



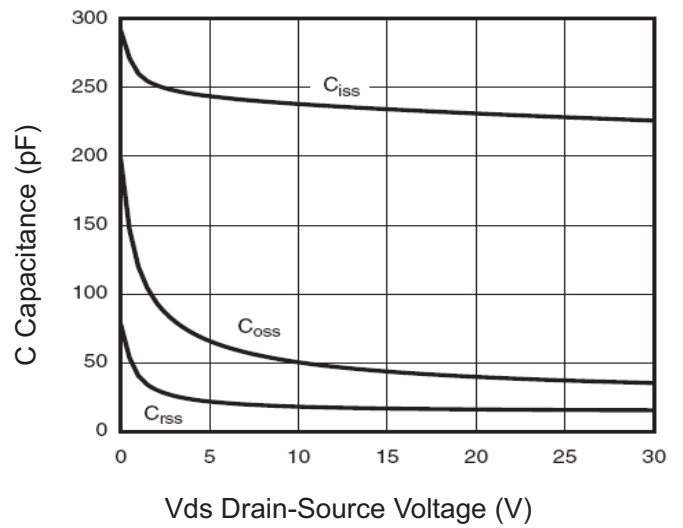
Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



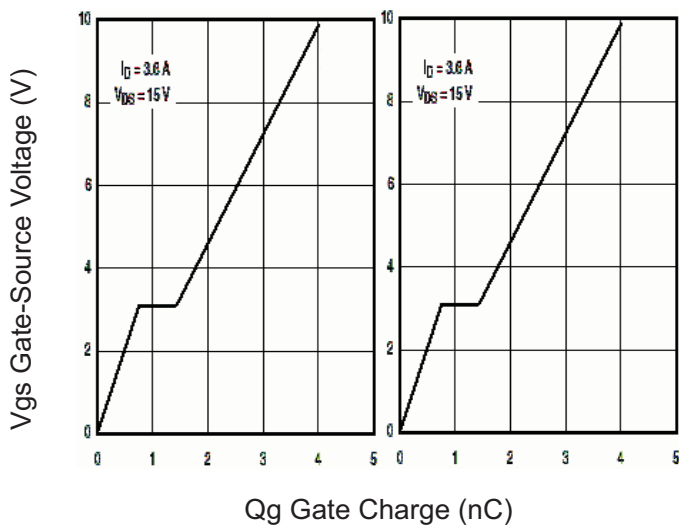
T_J -Junction Temperature($^\circ\text{C}$)
Figure 8 Drain-Source On-Resistance



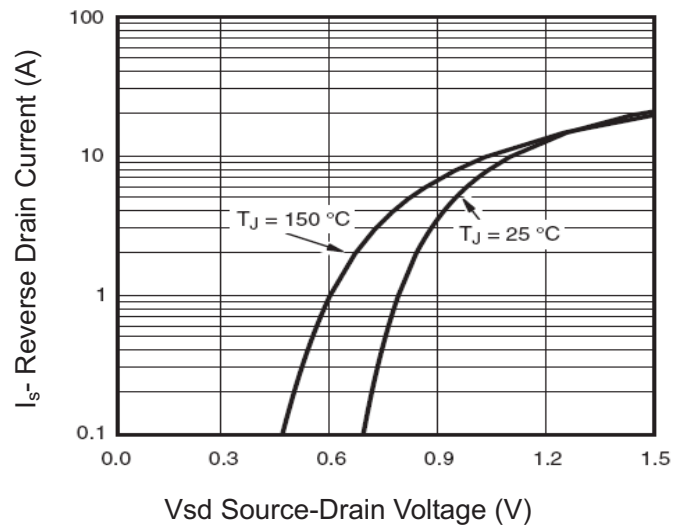
Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs



V_{DS} Drain-Source Voltage (V)
Figure 10 Capacitance vs Vds



Qg Gate Charge (nC)
Figure 11 Gate Charge



V_{SD} Source-Drain Voltage (V)
Figure 12 Source- Drain Diode Forward

RATING AND CHARACTERISTICS CURVES (RM3A6N30S2)

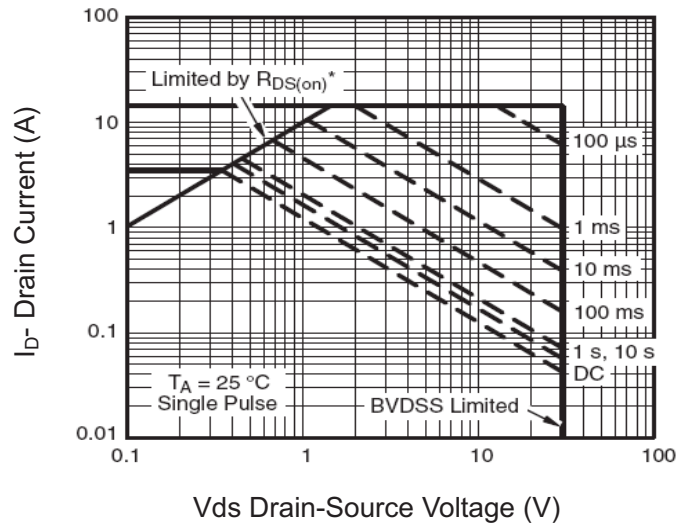


Figure 13 Safe Operation Area

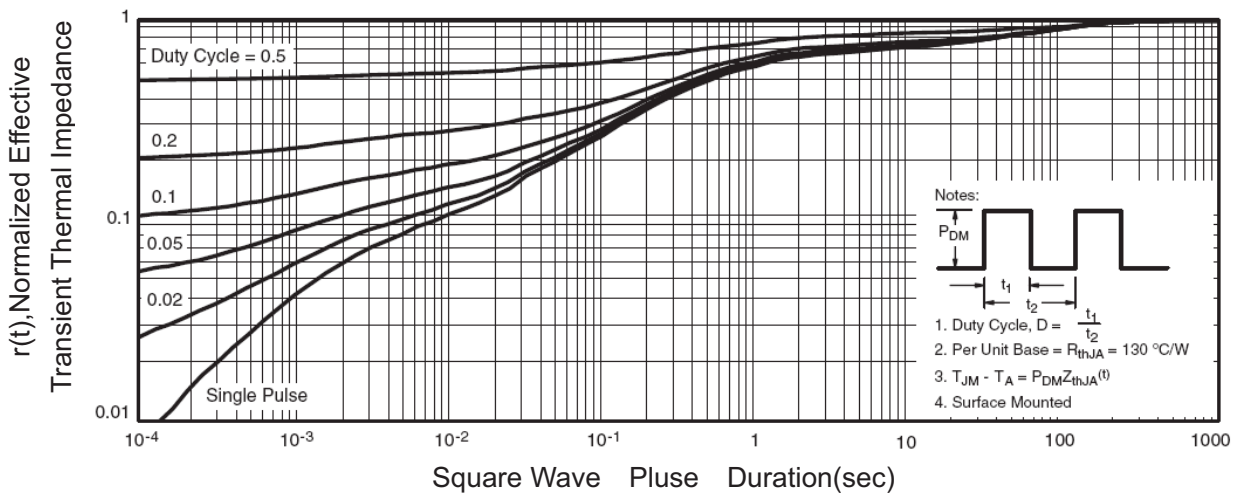
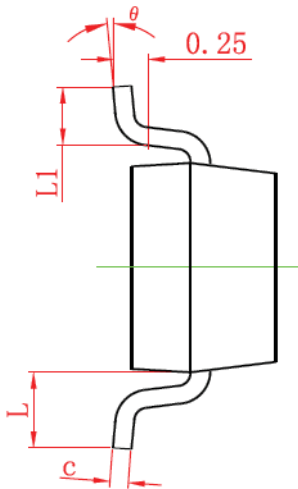
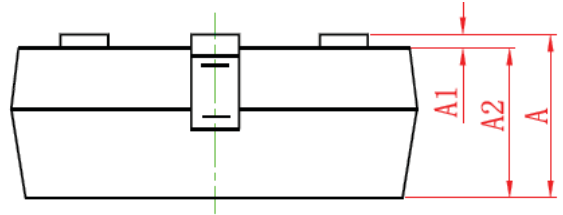
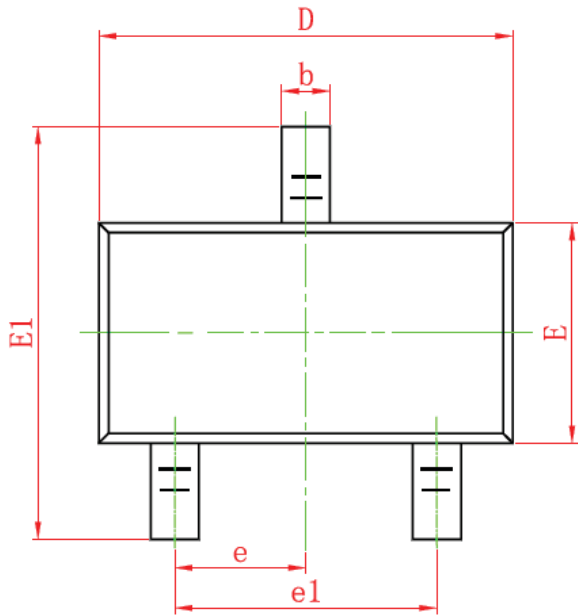


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

Notes

- All dimensions are in millimeters.
- Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
- Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- Dimension L is measured in gauge plane.
- Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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